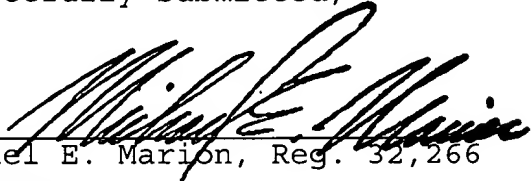


The claims were not amended in order to address issues of patentability and Applicant respectfully reserves all rights he may have under the Doctrine of Equivalents. Applicant furthermore reserves his right to reintroduce subject matter deleted herein at a later time during the prosecution of this application or continuing applications.

Respectfully submitted,

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APPENDIX

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3. (Amended) The arrangement according to claim 1 ~~or 2~~, wherein said second diffusion region (45) is an anode of a protection diode (9) and said second buried layer (12) is a cathode of said protection diode (9).

4. (Amended) The arrangement according to claim 1 ~~any of the preceding claims~~, wherein said first buried layer (12) is connected to said second buried layer (12), and said first and second buried layers (12) are manufactured in the same step.

5. (Amended) The arrangement according to claim 1 ~~any of the preceding claims~~, further comprising a channel stopper region (42) in said second portion of said substrate layer (13); the channel stopper region (42) being of said first conductivity type, for electrically isolating said second portion of said substrate layer (13) within the substrate (6), wherein said channel stopper region (42) is arranged to extend substantially as an extended channel stopper region (47) in between said second diffusion region (45) and said second buried layer (12), for reducing said second breakdown voltage.

8. (Amended) A method according to claim 6 ~~claims 6-7~~, further comprising the step of forming by ion-implantation a channel stopper region (42) in said second portion of said substrate layer (13); the channel stopper regions (42) being of said first conductivity type, for electrically isolating said second portion of said substrate layer (13) within the substrate (6) wherein said channel stopper region (42) is formed by ion-implantation as an extended channel stopper region (47) in between said second diffusion region (45) and

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said second buried layer (12), for reducing said second  
'breakdown voltage.

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